

Dual Adjustable Precision Shunt Regulator

FEATURES

- Low voltage operation (1.25V)
- Adjustable output voltage from $V_o = V_{REF}$ to 12V
- Wide operating current range from 55uA to 100mA
- Low dynamic output impedance 0.25Ω typ.
- ESD rating is 6kV (per MIL-STD 883D)

APPLICATIONS

- Linear Regulators
- Adjustable Supplies
- Switching Power Supplies
- Battery Operated Computers
- Instrumentation
- Computer Disk Drives

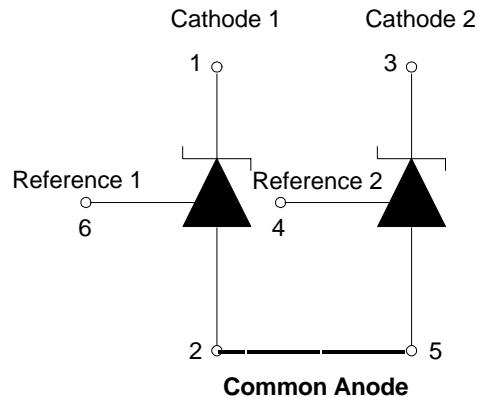
DESCRIPTION

The SS2432G consists of a pair of low-voltage adjustable shunt regulators with a guaranteed thermal stability over the applicable temperature range. The output voltage can be set to any value between V_{REF} (approximately 1.25V) to 12V with two external resistors (see application circuit). This device has a typical output impedance of 0.25 ohms. Active output circuitry provides very sharp turn-on characteristics, making this device an excellent replacement for Zener diodes in many applications.

The SS2432G is characterized for operation from 0°C to 105°C.

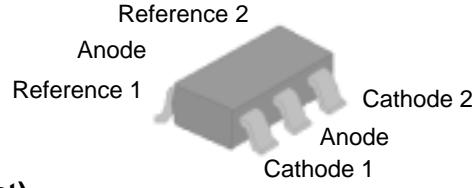
PIN CONFIGURATION

- Pin 1 : Cathode 1
- Pin 2 : Common Anode
- Pin 3 : Cathode 2
- Pin 4 : Reference 2
- Pin 5 : Common Anode
- Pin 6 : Reference 1



PACKAGE

The device is supplied in a SOT23-6 package.



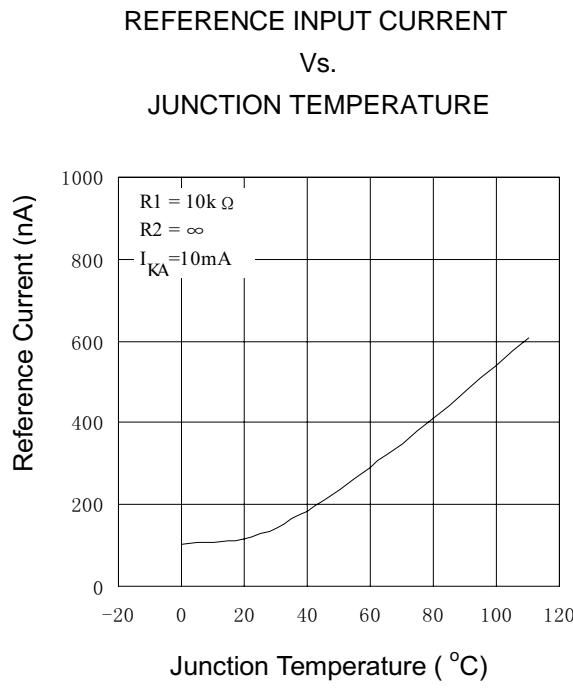
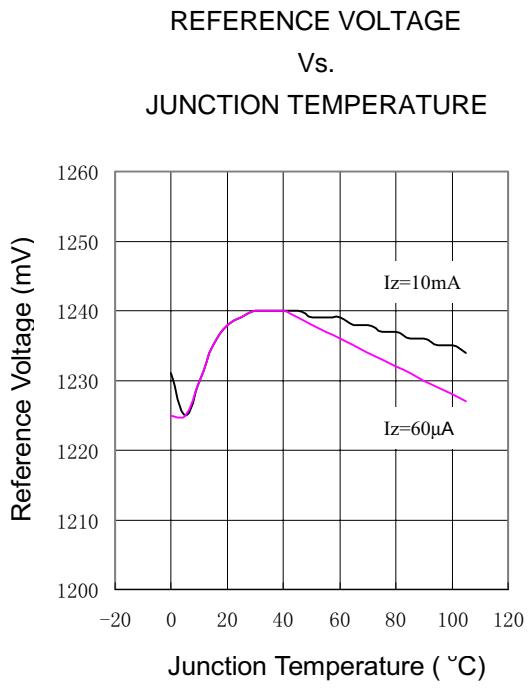
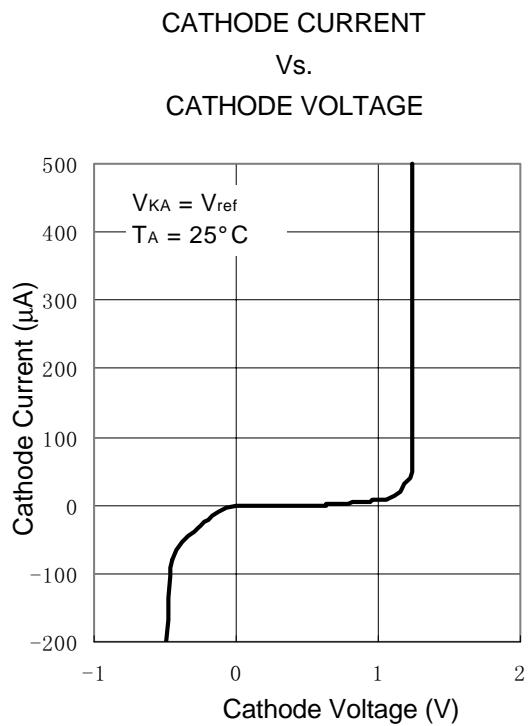
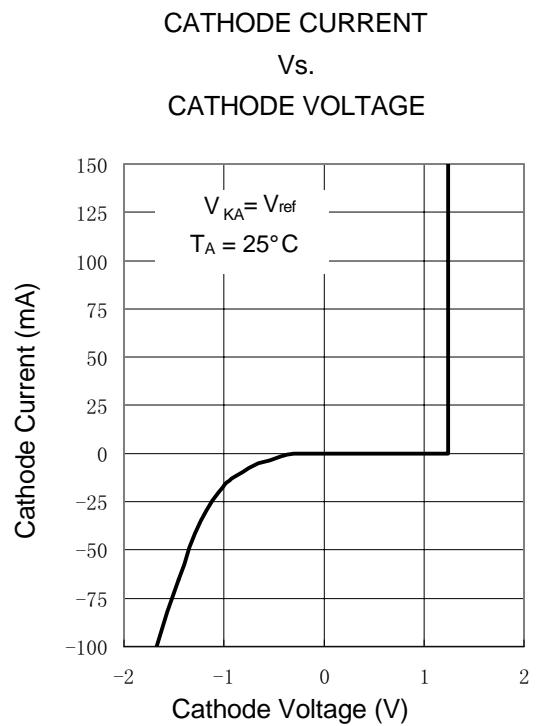
 Pb-free lead finish (second-level interconnect).

ABSOLUTE MAXIMUM RATINGS over ambient temp.range.

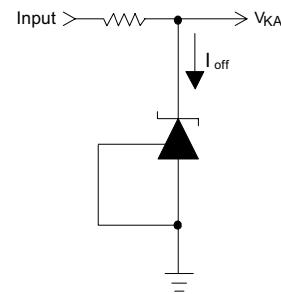
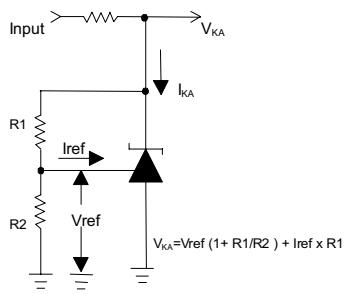
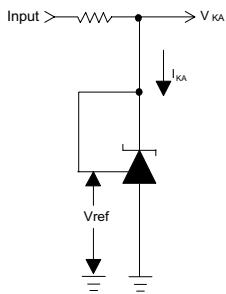
Parameter	Symbol	Maximum	Units
Cathode Voltage	V _{KA}	12	V
Continuous Cathode Current	I _{KA}	150	mA
Reference Current	I _{REF}	3	mA
Operating Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{STG}	-45 to +150	°C
Thermal Resistance	θ _{JA}	160	°C/W
Lead Temperature (Soldering - std.lead finish)	T _{LEAD}	260°C/10 sec.	

ELECTRICAL CHARACTERISTICS (T_A =25°C)

PARAMETER	SYMBOL	TEST CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reference voltage 1%	V _{ref}	1	V _{KA} = V _{ref} I _{KA} = 10mA	1.228	1.240	1.252	V
Deviation of reference voltage over full temperature range	V _{I(dev)}	1	V _{KA} = V _{ref} , I _{KA} = 10mA T _A = full range		4	12	mV
Ratio of change in reference voltage to the change in cathode voltage	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	2	I _{KA} = 10mA, ΔV _{KA} = V _{ref} to 12V		-1.5	-2.7	mV/V
Reference current	I _{ref}	2	I _{KA} = 10mA, R ₁ = 10kΩ, R ₂ = ∞		0.15	0.5	μA
Deviation of reference current over full temperature range	I _{I(dev)}	2	I _{KA} = 10mA, R ₁ = 10kW, R ₂ = ∞ T _A = full range		0.05	0.30	μA
Minimum cathode current for regulation	I _{min}	1	V _{KA} = V _{ref}		55	80	μA
Off-state cathode current	I _{off}	3	V _{KA} = 12V, V _{ref} = 0		0.001	0.1	μA
Dynamic impedance	Z _{KA}	1	I _{KA} = 100μA to 100mA, V _{KA} = V _{ref} f ≤ 1kHz		0.25	0.4	Ω

TYPICAL PERFORMANCE CHARACTERISTICS


TEST CIRCUITS

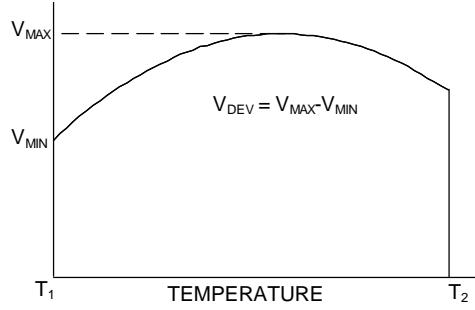


Test Circuit 1:
 $V_{KA} = V_{ref}$

Test Circuit 2:
 $V_{KA} > V_{ref}$

Test Circuit 3:
Off State Current

APPLICATION INFORMATION



Deviation of reference input voltage, V_{DEV} , is defined as the maximum variation of the reference input voltage over the full temperature range.

The average temperature coefficient of the reference input voltage, αV_{REF} , is defined as:

$$\Delta V_{REF} \frac{\text{ppm}}{\text{°C}} = \frac{\pm \left[\frac{V_{MAX} - V_{MIN}}{V_{REF}(\text{at } 25^{\circ}\text{C})} \right] 10^6}{T_2 - T_1} = \frac{\pm \left[\frac{V_{DEV}}{V_{REF}(\text{at } 25^{\circ}\text{C})} \right] 10^6}{T_2 - T_1}$$

Where:

$T_2 - T_1$ =full temperature change.

αV_{REF} can be positive or negative depending on whether the slope is positive or negative.

Example: $V_{DEV} = 12.0\text{mV}$, $V_{REF} = 1240\text{mV}$, $T_2 - T_1 = 105^{\circ}\text{C}$, slope is negative.

$$\alpha V_{REF} = \frac{\left[\frac{12.0\text{mV}}{1240\text{mV}} \right] 10^6}{105^{\circ}\text{C}} = -92\text{ppm/}^{\circ}\text{C}$$

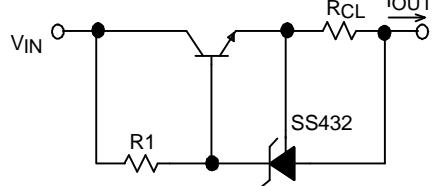
Note 4. The dynamic output impedance, R_Z , is defined as:

$$R_Z = \frac{\Delta V_Z}{\Delta I_Z}$$

When the device is programmed with two external resistors, R_1 and R_2 , (see Fig. 2), the dynamic output impedance of the overall circuit, is defined as:

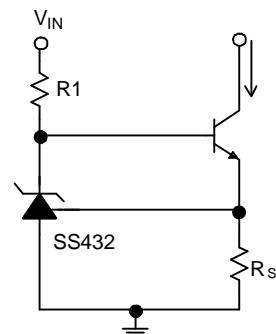
$$r_Z = \frac{\Delta V}{\Delta I} \approx R_Z \left[1 + \frac{R_1}{R_2} \right]$$

APPLICATION EXAMPLES



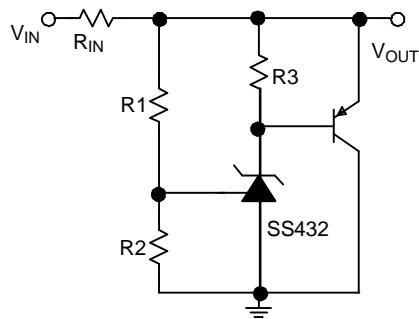
$$I_{OUT} = V_{REF} / R_{CL}$$

Current Limiter or Current Source



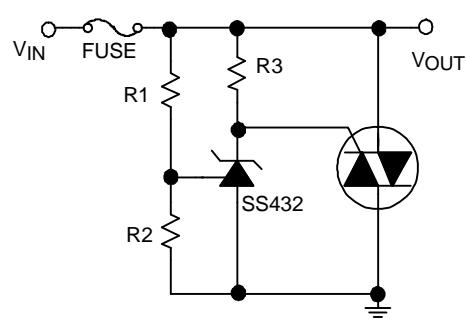
$$I_{OUT} = V_{REF} / R_s$$

Constant-Current Sink



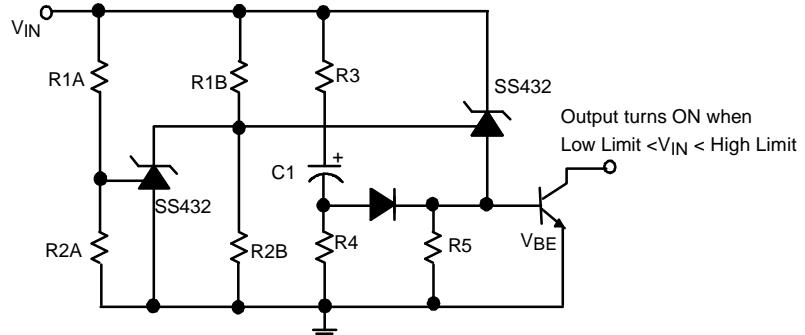
$$V_{OUT} \approx (1 + R_1/R_2) \times V_{REF}$$

Higher-Current Shunt Regulator



$$V_{LIMIT} \approx (1 + R_1/R_2) \times V_{REF}$$

Crow Bar

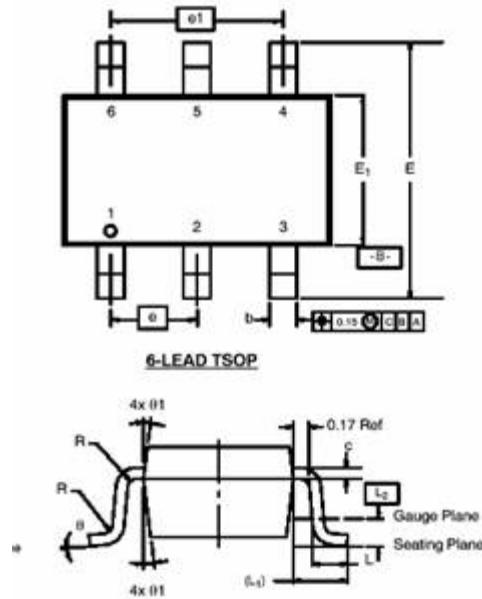


$$\text{Low Limit} \approx V_{REF} (1 + R_1B / R_2B) + V_{BE}$$

$$\text{High Limit} \approx V_{REF} (1 + R_1A / R_2A)$$

Over-Voltage/Under-Voltage Protection Circuit

PACKAGE DIMENSIONS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A₁	0.01	-	0.10	0.0004	-	0.004
A₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e₁	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L₁	0.60 Ref			0.024 Ref		
L₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ₁	7° Nom			7° Nom		
ECN: C-03247—Rev. G, 01-Sep-03 DWG: 5540						

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